

SILICON PLANAR VARIABLE CAPACITANCE DIODES

The BB105A is intended for use in u.h.f. tuners up to frequencies of 790 MHz.

The BB105B is meant for u.h.f. tuners up to frequencies of 860 MHz.

The BB105G is meant for v.h.f. tuners.

Twelve matched diodes are delivered together, thus containing 4 triplets or 3 quadruplets.

The capacitance difference between any two of the twelve diodes is less than 3% for the BB105A and BB105B and less than 6% for the BB105G over the voltage range from 0.5 to 28 V.

QUICK REFERENCE DATA

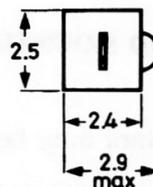
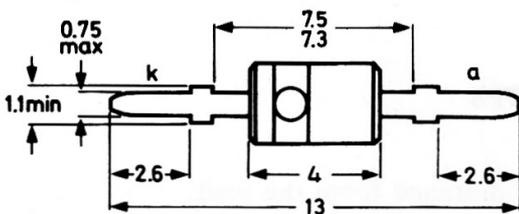
Reverse voltage	V_R	max.	28	V		
Reverse current at $V_R = 28$ V	I_R	<	100	nA		
Diode capacitance at $f = 1$ MHz $V_R = 25$ V	C_d		BB105A	BB105B	BB105G	
		>	2.3	2.0	1.8	pF
		<	2.8	2.3	2.8	pF
Capacitance ratio at $f = 1$ MHz $\frac{C_d(V_R = 3 \text{ V})}{C_d(V_R = 25 \text{ V})}$		>	4	4.5	4	
		<	5	6	6	
Series resistance at $f = 470$ MHz V_R is that value at which $C_d = 9$ pF	r_D	typ.	0.6	0.6	0.9	Ω
		<	0.7	0.7	1.2	Ω

MECHANICAL DATA

Dimensions in mm

12-BB105A and B: marked on packing
12-BB105G : green dot on the envelope

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The white band indicates the cathode side

The sealing of the plastic envelope withstands the accelerated damp heat test of IEC recommendation 68-2 (test D, severity IV, 6 cycles).

RATINGS Limiting values in accordance with the Absolute Maximum System (IEC 134)-

Continuous reverse voltage	V_R	max. 28 V
Reverse voltage (peak value)	V_{RM}	max. 30 V
Forward current (d.c.)	I_F	max. 20 mA
→ Storage temperature	T_{stg}	-55 to +100 °C
Junction temperature	T_j	max. 60 °C

THERMAL RESISTANCEwww.datasheetcatalog.comFrom junction to ambient in free air $R_{th\ j-a} = 0.4\text{ °C/mW}$ **CHARACTERISTICS** $T_j = 25\text{ °C}$ unless otherwise specifiedReverse current

		BB105A	BB105B	BB105G
$V_R = 28\text{ V}$	$I_R <$	100	100	100 nA
→ $V_R = 28\text{ V}; T_j = 60\text{ °C}$	$I_R <$	0.5	0.5	0.5 μA

Diode capacitance at $f = 1\text{ MHz}$

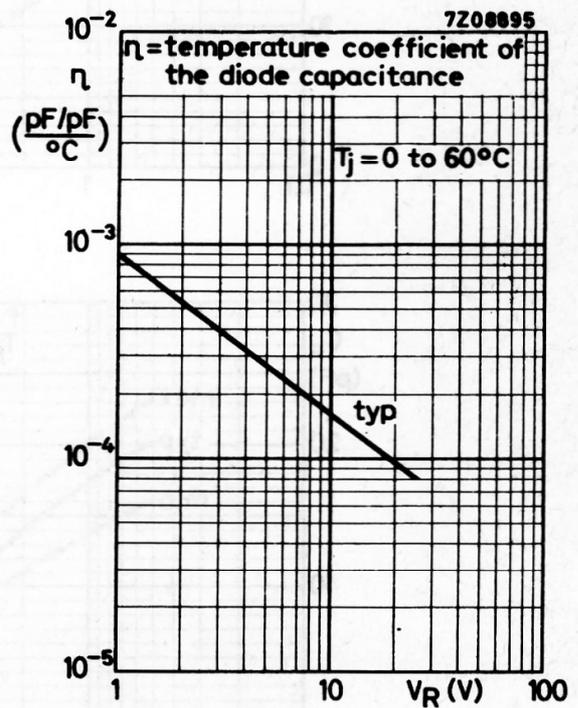
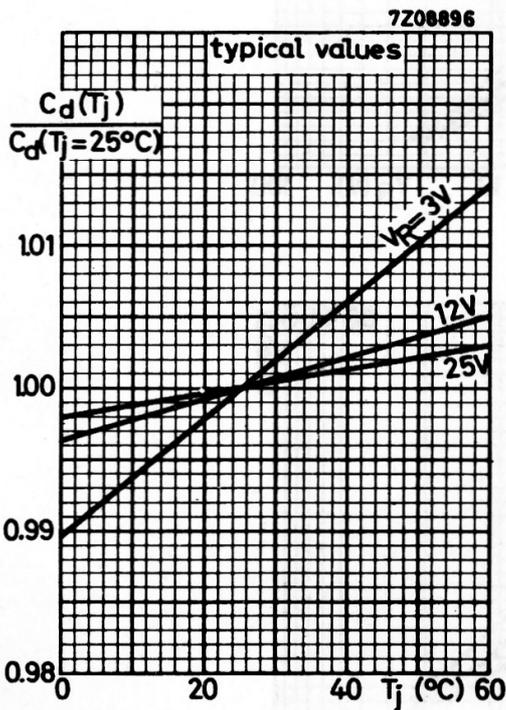
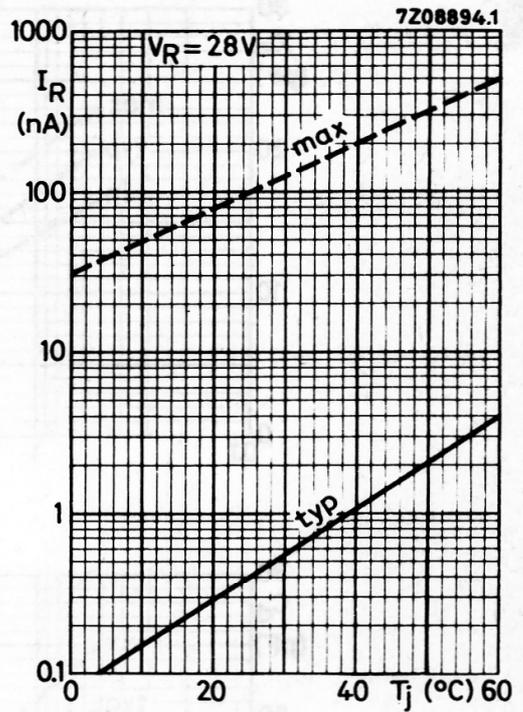
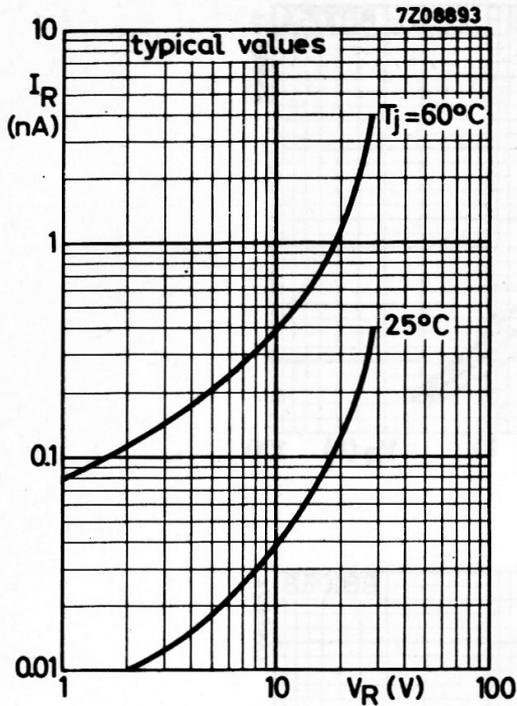
$V_R = 1\text{ V}$	C_d typ.	17	17.5	17.5 pF
$V_R = 3\text{ V}$	C_d typ.	11.5	11.5	11.5 pF
$V_R = 25\text{ V}$	$C_d >$	2.3	2.0	1.8 pF
	$C_d <$	2.8	2.3	2.8 pF
<u>Capacitance ratio at $f = 1\text{ MHz}$</u>	$\frac{C_d(V_R = 3\text{ V})}{C_d(V_R = 25\text{ V})} >$	4	4.5	4
	$\frac{C_d(V_R = 3\text{ V})}{C_d(V_R = 25\text{ V})} <$	5	6	6

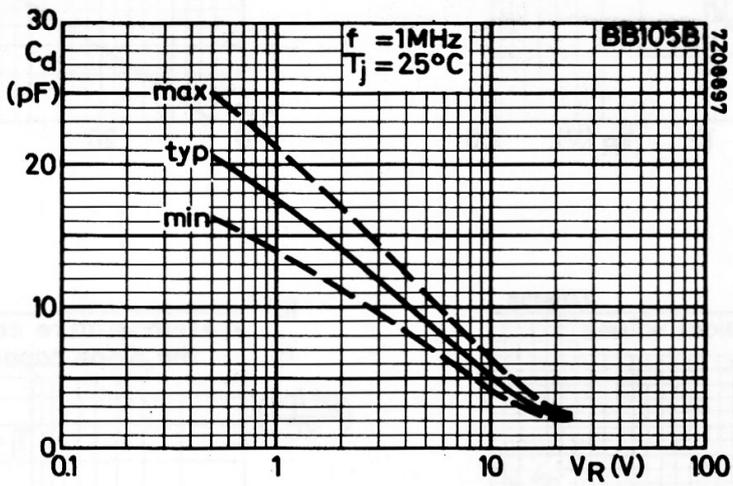
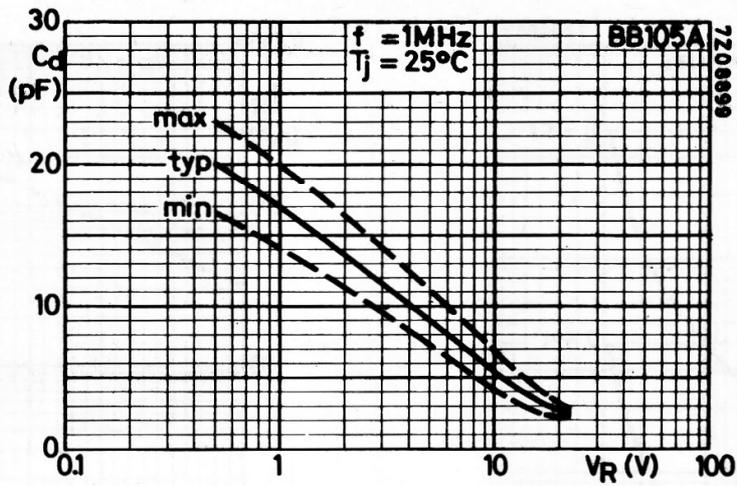
Series resistance

→ at $f = 470\text{ MHz}$ and at that value of V_R at which $C_d = 9\text{ pF}$	r_D typ.	0.6	0.6	0.9 Ω
	$r_D <$	0.7	0.7	1.2 Ω
at $f = 200\text{ MHz}$ and $I_F = 5\text{ mA}$	r_D typ.	0.4	0.4	0.4 Ω

SOLDERING AND MOUNTING NOTES

- Soldered joints may be at any distance from the seal.
- The maximum permissible temperature of the soldering iron or bath is 300 °C; it must be in contact with the joint for no more than 3 seconds.
- Avoid hot spots due to handling or mounting; the body of the device must not come into contact with or be exposed to a temperature higher than 125 °C.
- Leads should not be bent less than 0.5 mm from the seal; exert no axial pull when bending.





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